

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

- MJE200
Low collector-emitter saturation voltage, high current gain bandwidth product, Complement to MJE200.

Designed for general audio amplifier applications.

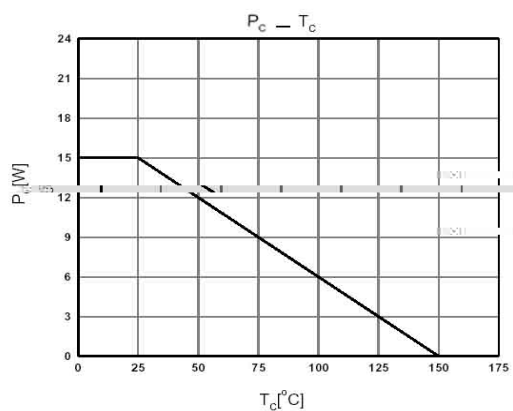
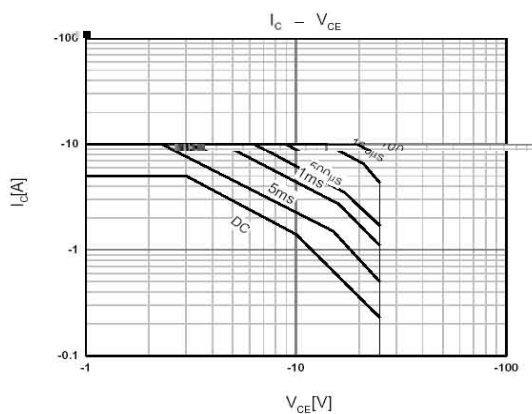
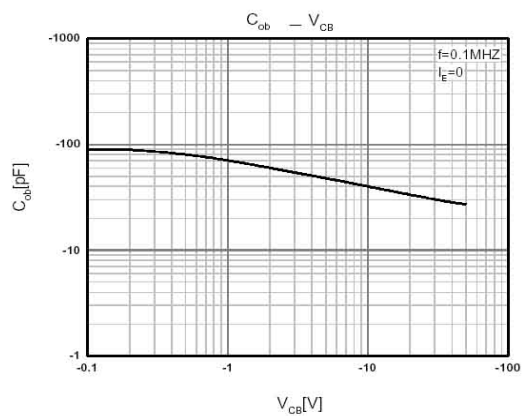
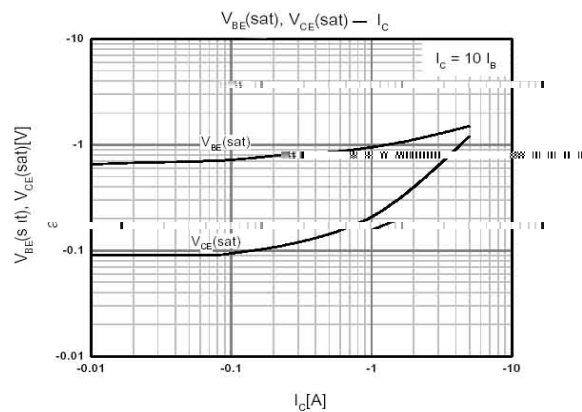
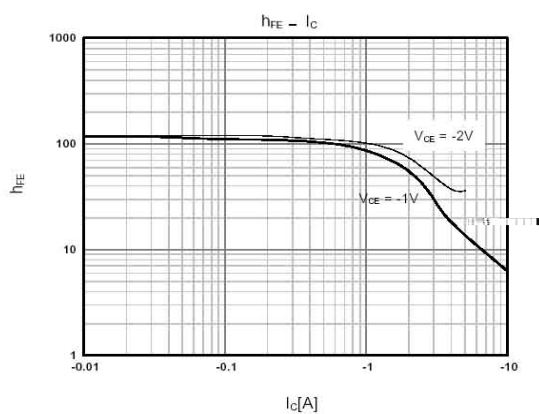
PIN1	Emitter	PIN 2	Collector	PIN 3	Base
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- See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-8.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Power Dissipation	$P_C(T_C=25^{\circ}C)$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

 Parameter

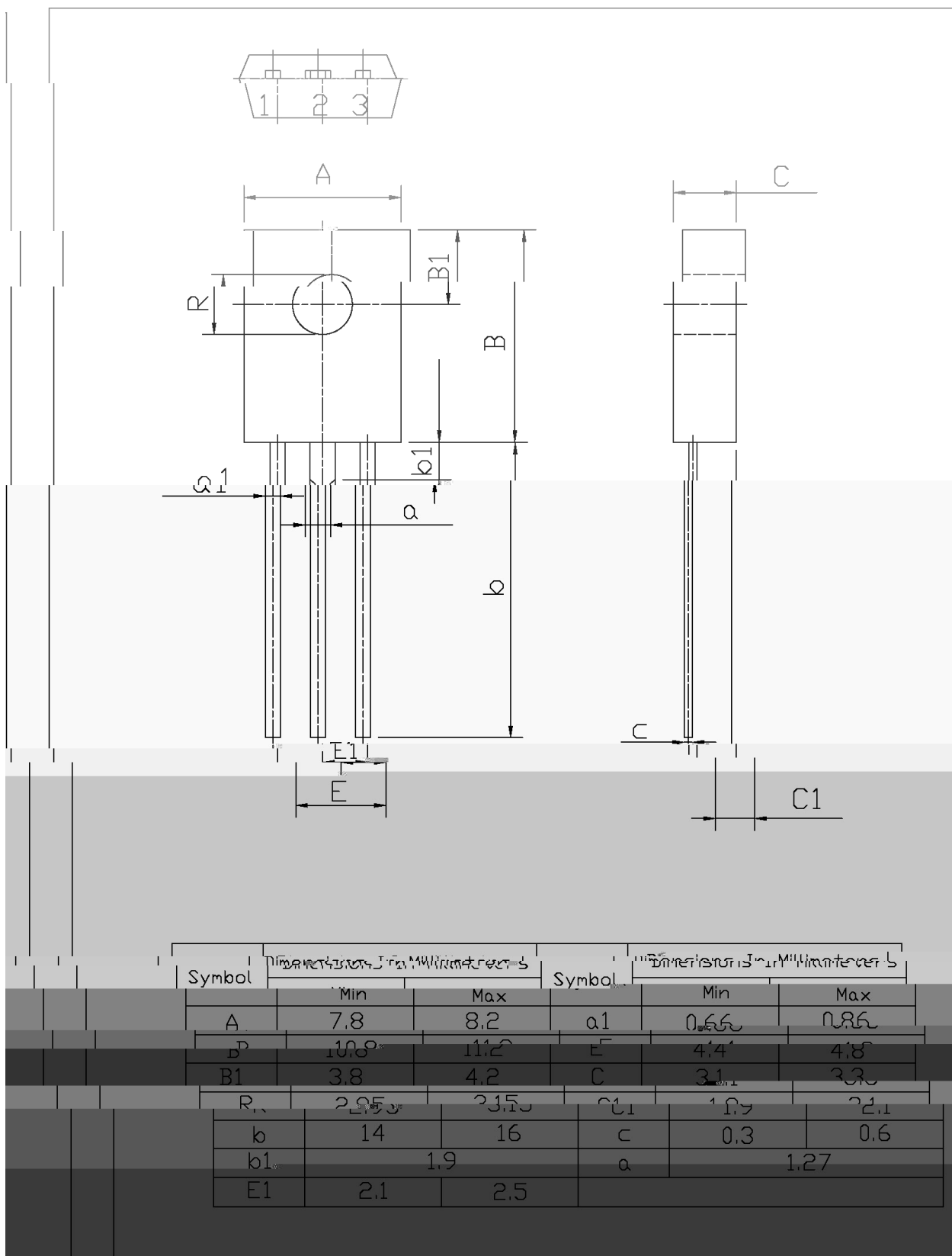
/ Electrical Characteristic Curve



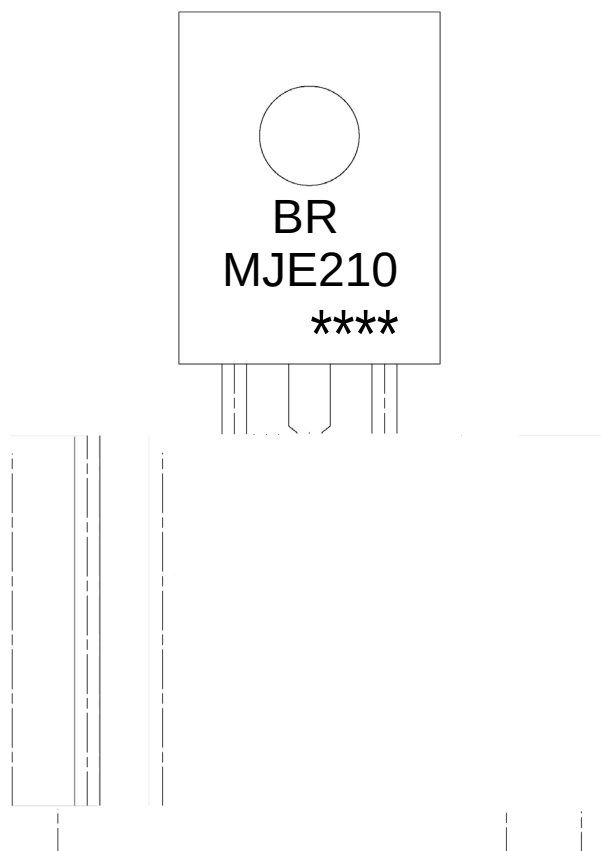
/ Package Dimensions

TU-126T

单位: mm



/ Marking Instructions



BR

MJE210

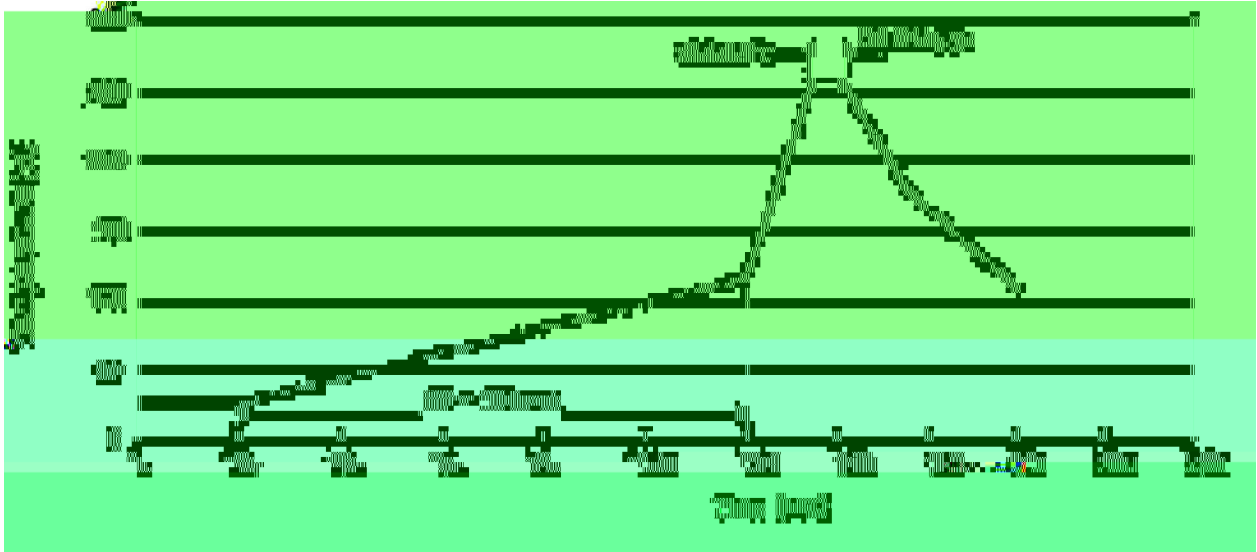
Note:

BR: Company Code

MJE210: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-126/F	65	26	1,690	5	8,450	532×31×5.6	555×164×50	575×290×180

/ Notices